

## ABSTRACT OF THE DISCLOSURE

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A wet treatment method useful in at least one of a chemical processing step and a rinsing step performed upon fabrication of semiconductor devices is disclosed. According to this method, a substrate under treatment is treated with a desired liquid while causing the substrate to revolve around an axis of rotation outside the substrate itself instead of allowing the substrate to rotate about the axis of rotation such that the liquid flowing on a surface of the substrate is maintained flowing under a centrifugal force greater than gravitation. The substrate is treated while supplying a fresh liquid of the same kind as the desired liquid at a flow rate at least equal to a discharge rate of the desired liquid only in a direction conforming with that of the centrifugal force or with that of a flow of the liquid flowing on the surface of the substrate under the centrifugal force. The substrate is, therefore, evenly treated at the surface thereof with the desired liquid while avoiding development of such a situation that flows of the liquid run against each other on the surface of the substrate or a flow of the liquid stagnates on the surface of the substrate. A wet treatment apparatus suitable for use in practicing the wet treatment method is also disclosed.